NSN 5961-01-485-0162

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Diode Semiconductor Device - Page 1 of 1



View Online at https://aerobasegroup.com/nsn/5961-01-485-0162 **Inclosure Material:** Plastic **Overall Length:** Between 0.205 inches and 0.220 inches **Overall Height:** Between 0.075 inches and 0.095 inches Overall Width: Between 0.130 inches and 0.150 inches **Function For Which Designed:** Transient suppressor and unidirectional **End Application:** Aau, air combat maneuvering instruments Joint Electronic Device Engineering Council/jedec/case Outline Designation: Do-214aa **Mounting Method: Terminal Semiconductor Material:** Silicon Voltage Rating In Volts Per Characteristic: 39.05 breakdown voltage, dc and 33.30 working peak reverse voltage **Voltage Tolerance In Percent:** -5.0/+5.0 **Current Rating Per Characteristic:** 5.00 microamperes collector current, dc peak and 100.00 amperes forward current, average preset **Power Rating Per Characteristic:** 3.0 watts small-signal input power, common-collector absolute **Maximum Operating Tempurature Per Measurement Point:** 150.0 degrees celsius junction **Terminal Type And Quantity:** 2 printed circuit Shelf Life: N/a **Unit Of Measure: Demilitarization:** No